Tunable Fano Resonances Based on Two-beam Interference in Microring Resonator

Ting Hu  
Zhejiang University of Technology

Ping Yu  
National Cancer Institute at Frederick

Chen Qui  
Zhejiang University of Technology

Huiye Qui  
Zhejiang University of Technology

Fan Wang  
Chinese Academy of Sciences

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Tunable Fano resonances based on two-beam interference in microring resonator

Ting Hu, Ping Yu, Chen Qiu, Huiye Qiu, Fan Wang, Mei Yang, Xiaoqing Jiang, Hui Yu, Jianyi Yang

1Department of Information Science and Electronic Engineering, Zhejiang University, Hangzhou 310027, China
2Cyrus Tung Center for Sensor Materials and Applications, Zhejiang University, Hangzhou 310027, China
3Suzhou Institute of Biomedical Engineering and Technology, Chinese Academy of Sciences, Suzhou 215163, China
4Department of Electrical and Computer Engineering, University of Nevada, Las Vegas, Nevada 89154, USA

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In this paper, a resonant system is demonstrated on silicon-on-insulator wafer to achieve tunable Fano resonances. In this system, the Fano resonance originates from the interference of two beams resonant in the microring resonator. The shapes of the Fano resonances are tunable through controlling the phase difference of the two beams. Both large slope and high extinction ratio (ER) are obtained when the phase difference is 0.5π or 1.5π. Experimental results show that Fano resonances with steep slope and ER over 20dB are achieved in the whole free spectral range by controlling the microheaters to meet the phase condition. © 2013 American Institute of Physics.

Fano resonance, which results from interference between a resonance pathway and a coherent background pathway, has attracted broad research interests due to its potential application in high-sensitivity sensing and low power optical switching/modulating. A lot of theoretical and experimental works have been done to obtain the sharp asymmetric Fano resonances. In Ref. 2, Fan proposed the side-coupled waveguide-cavity systems to generate sharp Fano resonance and proved that its performance is greatly improved compared to the counterpart with symmetric line shape. Based on this model, Chao and Guo experimentally demonstrated the sensitive biochemical sensors. Mario et al. composed a two-ring resonator configuration to produce sharp Fano resonances to provide the optical switching with high extinction ratio (ER), large modulation depth (MD), and low switching threshold. The advantages compared with the conventional one-ring configuration were also considered in this work. Recently, Li et al. showed the possibility to control the Fano resonance in indirectly coupled whispering-gallery micro-resonators.13

The transmission spectrum of a single microring resonator (MRR) typically exhibits symmetric Lorentz line shape. But if two coherent lights (phase difference is not equal to 0 or π) are sent into the MRR simultaneously, the interference of the two beams destroys the optical power’s symmetric distribution on the two sides of the resonant wavelength, and subsequently leads the transmission spectrum to be an asymmetric Fano resonance. In this letter, we design and demonstrate a microring resonator-based two-beam interferometer (MRR-TBI) on silicon-on-insulator (SOI) to produce tunable Fano resonances. Two microheaters are addressed to tune the line shapes and resonant wavelengths, respectively, by utilizing the thermo-optic (TO) effect of silicon. The relationship between the spectral slope and phase difference of the two beams is theoretically analyzed. Based on the analysis results, by controlling the two heaters, we can obtain the Fano resonances with both steep slope and relative high ER over the whole free spectral range (FSR).

The schematic structure of the MRR-TBI, as shown in Fig. 1(a), consists of a 1 × 2 multi-mode interference (MMI) power splitter and a MRR. The two arms of the MMI splitter are also the bus waveguides of the MRR. The two coupling regions have the field coupling coefficient of ki and k2. In the configuration, the input beam will be divided to two parts by the 1 × 2 MMI splitter and then partly coupled into the MRR through the two coupling zones. E1 and E2 are the electric fields of the input bus waveguides, while Eo1 and Eo2 represent that of the output bus waveguides. The optical transmission spectra of the output ports can be derived by the transfer matrix method20,21 as

\[
P_{o1} = |E_{o1}|^2 = \left[ \frac{t_1 - t_2 \exp(j\theta)}{1 - \alpha t_1 t_2 \exp(j\theta)} \cdot \gamma \right]^2 + \alpha_c \cdot \left[ \frac{-2 \alpha \cdot k_1 k_2 \exp(\frac{\theta}{2})}{1 - \alpha t_1 t_2 \exp(j\theta)} \cdot (1 - \gamma)^{\frac{1}{2}} \cdot \exp(j\phi) \right]^2,
\]

\[
P_{o2} = |E_{o2}|^2 = \left[ \alpha_c \cdot \left( \frac{-2 \alpha \cdot k_1 k_2 \exp(\frac{\theta}{2})}{1 - \alpha t_1 t_2 \exp(j\theta)} \cdot \gamma \right) \cdot \left[ \frac{t_2 - t_1 \exp(j\theta)}{1 - \alpha t_1 t_2 \exp(j\theta)} \cdot (1 - \gamma)^{\frac{1}{2}} \cdot \exp(j\phi) \right] \right]^2,
\]

Electronic mail: afterglow.yuhui@gmail.com.
Electronic mail: yangji@zju.edu.cn.
The coupling between the bus and ring waveguides is assumed lossless so that the self and cross coupling coefficients $k$ and $t$ satisfy $k_i^2 + t_i^2 = 1 \ (i = 1, 2)$. $\theta = \frac{4\pi n_{\text{eff}}R}{\lambda}$ is the single-pass phase shift of the ring, where $R$ is the radius of the ring, $\lambda$ is the optical wavelength, and $n_{\text{eff}}$ is the effective refractive index of waveguides.

In the ideal condition, the input light will be divided to two beams with equal power, so $\gamma$ is assumed to be 0.5. According to Eq. (1), the calculated transmission spectra of $P_{o1}$ and $P_{o2}$ at the resonance around 1544.4 nm are shown in Fig. 2. We can see from the figures that both the Fano-resonance line shapes of $P_{o1}$ and $P_{o2}$ vary with $\varphi$, except when $\varphi = 0$ or $\varphi = \pi$ the transmission line shapes exhibit symmetric profiles. Notice that the spectra for $P_{o1}$ ($P_{o2}$) at $\varphi = \zeta$ ($\zeta$ is an arbitrary angle from 0 to $2\pi$) and $\varphi = 2\pi - \zeta$ are horizontal mirror-symmetric. Obviously, the Fano-resonance line shapes can be controlled by tuning the value of $\varphi$. In the simulation, $k_1 = k_2 = 0.25$, $\alpha = 0.9928$, and $\alpha_c = 0.95$ are assumed, respectively.

The physical dimension of the MRR-TBI is determined by the numerical simulation. The structure optimizing the $1 \times 2$ MMI splitter is simulated by employing the three-dimensional beam propagation method (BPM). The width and length of the MMI waveguide, in which the self-image effect happens, are 9 and 75.25 $\mu$m, respectively. The input port is located at the center of the left side, while the two output ports are set 2.25 $\mu$m away from the center at the right side. A 40-$\mu$m-long linear tapered waveguide provides an adiabatic transition between the interconnecting waveguides and the 1.2-$\mu$m-wide MMI access waveguides. The interconnecting and ring waveguides are designed with a cross section of 450 $\times$ 220 nm$^2$ and all waveguides are with a 60-nm-thick slab. The 10-μm-radius ring is chosen to obtain a FSR around 10 nm. The relationship of the coupling coefficient and the gap between bus and ring waveguides are calculated using three-dimensional finite-difference time-domain (FDTD) method. The gap of 300 nm is selected to obtain a trade-off among the ER, optical bandwidth, and drop insertion loss of the MRR. The FDTD method is also employed to optimize the ellipse-based crossing waveguide in the lower output arm of the MMI splitter. For realizing low transmission loss and lateral crosstalk, the long and short axes of that are chosen to be 8 and 2 $\mu$m, respectively. To control the Fano-resonance line shapes, one microheater ($H_1$) is placed over the lower arm of the MMI splitter to change $\varphi$ through TO effect. Another microheater ($H_2$) over the ring is proposed to tune the resonant wavelength of the Fano resonance.

The device is fabricated on a SOI wafer with 220-nm-thick top silicon layer and 2-μm-thick buried dioxide layer. The 248-nm deep ultraviolet (UV) photolithography is used to define the device pattern. Inductively coupled plasma etching process is adopted to etch the top silicon layer. The gratings couplers, covering layer, via, 120-nm-thick TiN microheaters, aluminum wires, and pads are fabricated with the same process in Refs. 22 and 23. The top-view optical micrograph of a typical fabricated device is shown in Fig. 1(b).

The fabricated device is characterized by using an amplified spontaneous emission (ASE) source, an optical spectrum analyzer (OSA), and two tunable voltage sources. The broadband light is coupled into the device through the grating coupler. The output light is collected by another grating coupler and fed into the OSA. The two voltage sources are used to drive the two TiN heaters. Fig. 3(a) shows the measured TE-polarized (electric field parallel to the chip) transmission spectra for the two output ports without biasing $H_1$ and $H_2$. Both $P_{o1}$ and $P_{o2}$ exhibit asymmetric resonant line shapes. Due to the transmission loss caused by the crossing waveguide, the insertion loss of the $p_{o2}$ is larger than that of $P_{o1}$. The Fano resonance of $P_{o1}$ reaches an ER $\approx 20$ dB, which is slightly smaller than that of $P_{o2}$. The quality factor is observed to be around $1.08 \times 10^4$. To tune the line shapes, biases of 6 to 10 V with 1 V increment are applied to $H_1$. The measured transmission spectra are shown in Figs. 3(b)–3(f). At 9 V bias, near symmetric spectra are observed. As the voltage increases continuously, as shown in Fig. 3(f), the transmission spectra become Fano resonances again. But the line shapes trend to be swapped compared to those with bias under 9 V. In order to accurately control the Fano line shapes, we fit the measured transmission spectra by using Eq. (1), to analyze the value of $\varphi$. The corresponding
and $P_{o2}$ at the resonant wavelengths ($\theta = 2m\pi$, $m$ is an integer) can be derived from Eq. (1) as

$$S_1 = \frac{\alpha_c [\gamma (1 - \gamma)]^{1/2} k_1 k_2 (t_1 + x t_2) \sin \varphi}{(1 - \alpha t_1 t_2)^2},$$

$$S_2 = \frac{\alpha_c [\gamma (1 - \gamma)]^{1/2} k_1 k_2 (2 t_1 + t_2) \sin \varphi}{(1 - \alpha t_1 t_2)^2},$$

(2)

It is clear, from Eq. (2), when $\varphi$ is equal to $\pi/2$ or $3\pi/2$, slopes have the maximum value. According to previous theoretical analysis, the line shapes of $P_{o1}$ ($P_{o2}$) at $\varphi = \pi/2$ and $\varphi = 3\pi/2$ are mirror-symmetric. Thus, tuning the transmission spectra to be the same or mirror-symmetric with that shown in Fig. 3(a) can obtain a sharp asymmetric line shape with an ER over 20 dB. Figs. 4(a) and 4(b) display the Fano resonant wavelengths of $P_{o1}$ and $P_{o2}$ tuned over the whole FSR by utilizing $H_2$ to heat the MRR. Because of the wavelength dispersion of $n_{eff}$, $\varphi$ for each resonance is different, which leads those resonances to present various shapes. By controlling $H_1$ to compensate the phase shift caused by the wavelength dispersion, sharp Fano resonances with ER over 20 dB are obtained in the whole FSR (Figs. 4(c) and 4(d)). The applied voltages on $H_2$ for shifting the resonant wavelength and on $H_1$ for achieving the sharp line shape are listed in Table I.

In Figs. 4(a) and 4(b), resonances #3 and #5 have the similar gesture, but after tuned to sharp line shapes, they become mirror-symmetric gesture, as shown in Figs. 4(c) and 4(d). It is because that $\varphi$ at #3 is close to but less than $2\pi$, while $\varphi$ at #5 is close to but larger than $\pi$. As voltage is applied to $H_1$, $\varphi$ decreases. At #3, it decreases to $3\pi/2$ without pasting the gesture flip point ($\varphi = 0$ or $\pi$). Oppositely, $\varphi$ at #5 decreases to $\pi/2$ and pasts the gesture flip point ($\varphi = \pi$), thus the gesture is changed. To resolve the problem, we can add one more heater over the other output arm of the MMI splitter so that it is flexible to increase or decrease $\varphi$ rather than can only decrease it in our demonstrated device.

In summary, we experimentally demonstrate a MRR-TBI that can generate Fano resonances. The device is fabricated on SOI wafer by the complementary metal-oxide-semiconductor (CMOS) compatible process. The Fano-resonance line shapes are well controlled by tuning the phase difference between the two lights fed into the MRR through the TO effect of silicon. By utilizing the heaters $H_1$ and $H_2$ to satisfy the phase condition, Fano resonances are tuned to those with sharp slope and ER over 20 dB in the whole FSR, which leads the fabricated device potential to apply in high-sensitivity sensing and low power optical switching/modulating.

![Fig. 3. (a)–(f) Measured output-port transmission spectra of the MRR-TBI with various bias voltages on $H_2$. (g)–(l) Modeled corresponding output-port transmission spectra. (m) Analyzed TO effect-induced phase shifts.](image)

![Fig. 4. Measured output-port transmission spectra of the MRR-TBI (a) and (b) before and (c) and (d) after tuned to be sharp line shapes with high ER over the whole FSR.](image)
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9A. E. Miroshnichenko and Y. S. Kivshar, Rev. Mod. Phys. 82, 2257 (2010).

<table>
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<th>Fano resonance</th>
<th>#1</th>
<th>#2</th>
<th>#3</th>
<th>#4</th>
<th>#5</th>
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<td>8</td>
<td>9.02</td>
<td>10</td>
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TABLE I. Voltages applied on $H_1$ and $H_2$.